


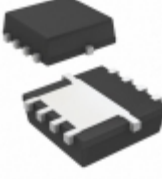




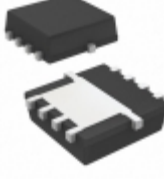
	<h2>SI7611DN-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7611DN-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 40V 18A 1212-8</p> <p>Datenblätter:  SI7611DN-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 47275 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7611DN-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 40V 18A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	47275 pcs Stock
detaillierte Beschreibung	P-Channel 40V 18A (Tc) 3.7W (Ta), 39W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-50°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	3.7W (Ta), 39W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	40V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	18A (Tc)
Rds On (Max) @ Id, Vgs	25 mOhm @ 9.3A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	62nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1980pF @ 20V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7611DN-T1-GE3TR

SI7611DN-T1-GE3 ist neu im Original, Suche SI7611DN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7611DN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7611DN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 SI7611DN SI SI7611DN SI	 SI7615ADN-T1-E3 VISHAY VISHAY PAK1212	 SI7613DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 35A 1212-8 PPAK	 SI7613DN-T1-E3 VISHAY VISHAY PAK1212
 SI7606DN-T1-GE3 VB SI7606DN-T1-GE3 VB	 SI7611DN-T1-E3 VISHAY SI7611DN-T1-E3 VISHAY	 SI7615ADN VISHAY VISHAY DFN33	 SI7613DN-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 35A 1212-8 PPAK

heiße Teile

Mehr

⊛ SI7483ADP-T1-GE3	↔ SI7483ADP-T1-GE3	⇒ SI7483DP-T1	D SI7483DP-T1-E3	↔ SI7483DP-T1-GE3
⊣ SI7485DP-T1-E3	⊛ SI7485DP-T1-E3	D SI7485DP-T1-GE3	⇒ SI7485DP-T1-GE3	↔ SI7489DP
⊛ SI7489DP-T1-GE3	⊣ SI7489DP-T1-GE3	⊛ SI7491DP	↔ SI7491DP-T1-GE3	↔ SI7491DP-T1-GE3
D SI7501DN-T1-E3	⊛ SI7501DN-T1-E3	⊣ SI7540ADP-T1-GE3	⊛ SI7540ADP-T1-GE3	↔ SI7540DP-T1-E3
⇒ SI7540DP-T1-E3	↔ SI7540DP-T1-GE3	⊛ SI7540DP-T1-GE3	⊣ SI7606DN-T1-E3	↔ SI7606DN-T1-GE3
↔ SI7611DN-T1-GE3	⇒ SI7613DN-T1-GE3	D SI7613DN-T1-GE3	⊛ SI7615ADN-T1-GE3	⊣ SI7615ADN-T1-GE3
⊛ SI7615DN	D SI7615DN-T1-E3	⇒ SI7615DN-T1-GE3	↔ SI7615DN-T1-GE3	↔ SI7617DN-T1-GE3
⊣ SI7617DN-T1-GE3	⊛ SI7619DN-T1-GE3	↔ SI7619DN-T1-GE3	⇒ SI7621DN-T1-GE3	↔ SI7621DN-T1-GE3
⊛ SI7625DN-T1-GE3	⊣ SI7625DN-T1-GE3	⊛ SI7629DN-T1	D SI7629DN-T1-GE3	↔ SI7629DN-T1-GE3
↔ SI7633DP-T1-GE3	⊛ SI7633DP-T1-GE3	⊣ SI7634BDP	⊛ SI7634BDP-T1-E3	↔ SI7634BDP-T1-E3

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